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The effect of surface passivation on the microwave characteristics of undoped AlGa_N/Ga_N HEMTs

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605	Microwave Al _x Ga _{1-x} N/GaN Power HEMTs. 2000 , 639, 821		
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600	Characteristics of AlGa _N /Ga _N HEMT devices with Si ₃ N ₄ passivation.		
599	Performance and limitations of AlGa _N /Ga _N HFETs grown on sapphire and SiC substrates.		3
598	Microwave performance of AlGa _N /Ga _N metal insulator semiconductor field effect transistors.		1
597	The gate-length dependent performance of AlGa _N /Ga _N HFETs with silicon nitride passivation.		2
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